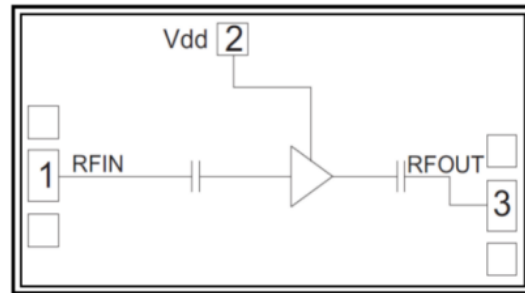


Features

- Single Biasing Voltage (Self Biased)
- Frequency: 6-18GHz
- Small Signal Gain: 22dB
- Noise Figure: 1.4dB typ. / 1.7dB max.
- P1dB: 2dBm
- Power Supply: +5 V/10 mA
- Input/Output: 50Ω
- Die Size: 1.85 x 0.95 x 0.09 mm

Typical Applications

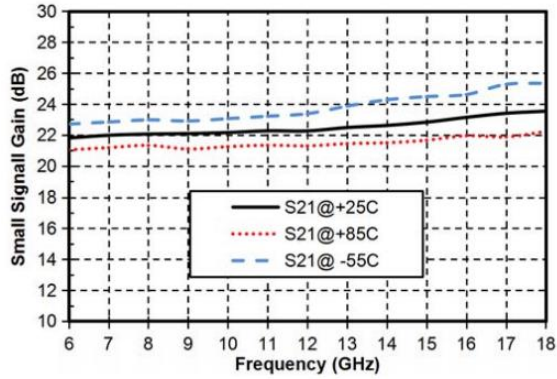
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Functional Block Diagram

Electrical Specifications
TA = +25°C, Vd = +5V

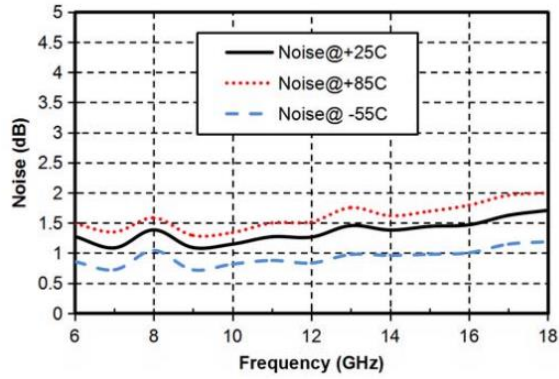
Parameters	Min.	Typ.	Max.	Units
Frequency	6-18			GHz
Small Signal Gain	21.5	22	23.5	dB
Gain Flatness		±1.0		dB
Noise Figure	-	1.4	1.7	dB
Output 1dB Compression (P1dB)		2		dBm
Saturated Output Power (Psat)		4		dBm
Input Return Loss	18	20	-	dB
Output Return Loss	17	20	-	dB
Static current		10		mA



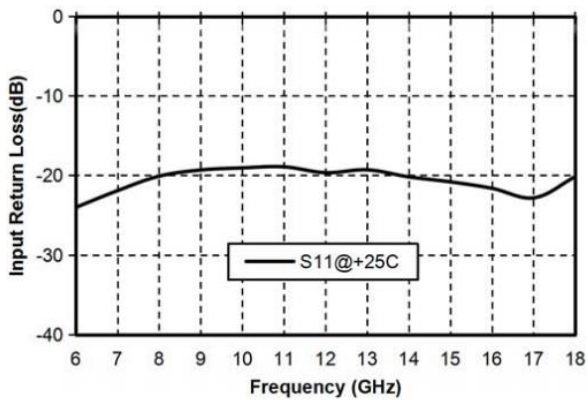
Gain vs. Temperature



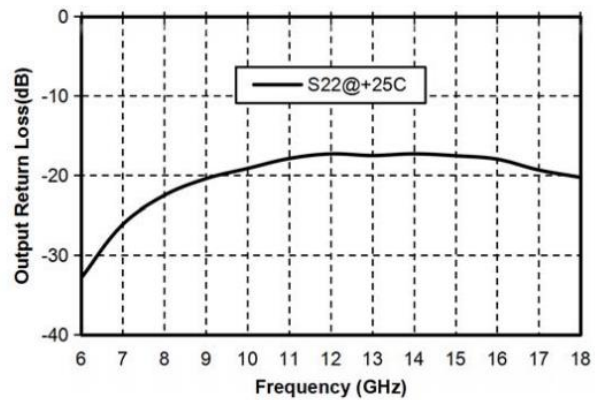
Noise Figure vs. Temperature



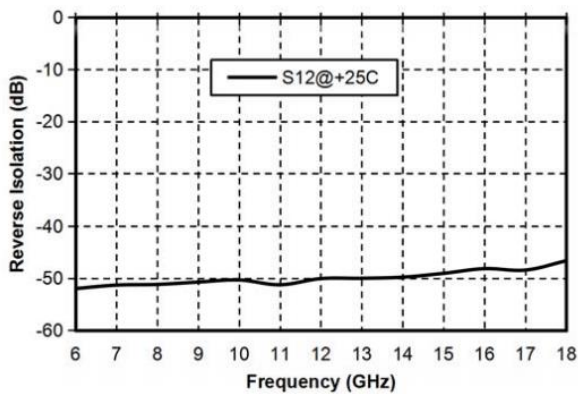
Input Return Loss vs. Frequency



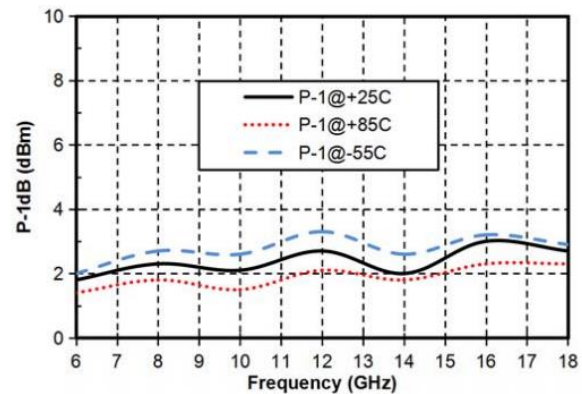
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

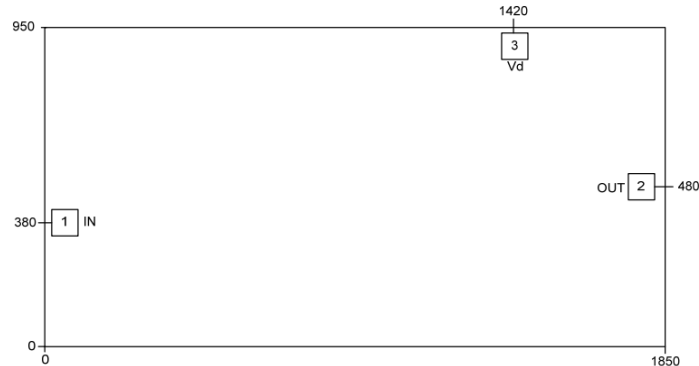


P1dB vs. Temperature





Outline Drawing:
All Dimensions in μm

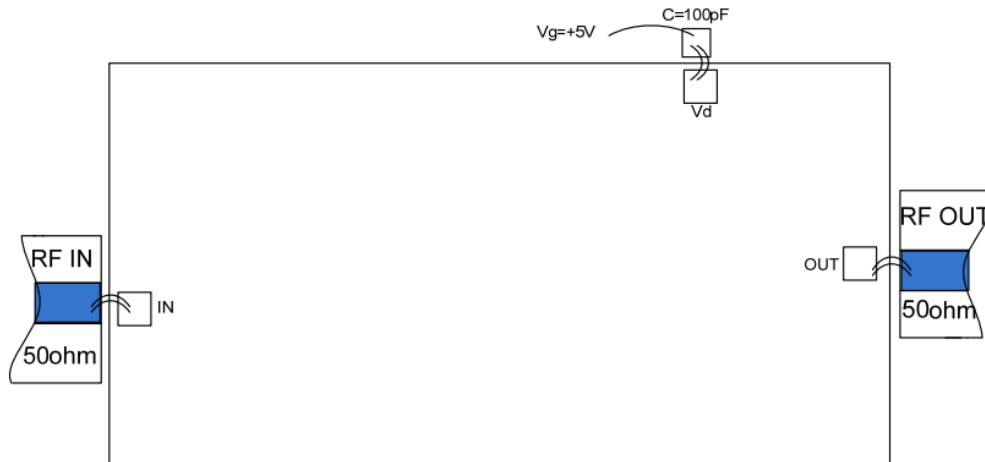


Pad Description

Pad	Function	Description
1	RF IN	RF signal input terminal, no blocking capacitor required.
2	RF OUT	RF signal output terminal, no blocking capacitor required.
3	Vd	Amplifier drain bias; external 100pF bypass capacitor required.
Die bottom	GND	Die bottom must be connected to RF/DC ground.



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C